

wherein the second flexible substrate is formed of a material having a coefficient of thermal expansion substantially equal to a coefficient of thermal expansion of a material of the first flexible substrate, and the first and second flexible substrates are of substantially the same thickness.

REMARKS

Claims 1 and 3-31 are pending. Claims 12-26 are withdrawn from consideration as being drawn to a non-elected Group. Rejoinder of claims 12-26 is respectfully requested. By this Amendment, claim 2 is cancelled without prejudice to or disclaimer of the subject matter contained therein, and claims 1, 4 and 29 are amended. Applicant amends claims 1, 4 and 29 to recite the features of claim 2. No new matter is added by any of these amendments.

Applicant appreciates the courtesies extended to Applicant's representative by Examiner Thai during the April 8, 2003 interview. The points discussed during the interview are incorporated in the remarks below and constitute Applicant's record of the interview.

Reconsideration based on the following remarks is respectfully requested.

The attached Appendix includes a marked-up copy of each rewritten claim (37 CFR §1.121(c)(1)(ii)).

I. Claims 1, 3-11 and 27-31 Define Patentable Subject Matter

The Office Action rejects claims 1, 3 and 29-31 under 35 U.S.C. §102(b) over U.S. Patent 5,255,430 to Tallaksen. This rejection is respectfully traversed. As discussed during the April 8 personal interview, claims 1 and 29, as amended, overcome Tallaksen. Withdrawal of the §102 rejection is respectfully requested.

The Office Action rejects claims 1-3, 10-11 and 29-31 under 35 U.S.C. §102(b) over U.S. Patent 5,926,696 to Baxter *et al.* (Baxter). This rejection is rendered moot with respect to claim 2 and respectfully traversed with respect to the remaining claims. As discussed

during the April 8 personal interview, claims 1 and 29, as amended, overcome Baxter.

Withdrawal of the §102 rejection is respectfully requested.

The Office Action further rejects claim 8 under 35 U.S.C. §103(a) over Tallaksen in view of U.S. Patent 6,140,707 to Plepys *et al.* (Plepys). This rejection is respectfully traversed.

As discussed during the April 8 personal interview, claim 1 as amended, from which claim 8 depends indirectly, overcomes Tallaksen. Because claim 1 would be allowable over Tallaksen, claim 8 should also be allowable. Withdrawal of the §103 rejection is respectfully requested.

The Office Action rejects claims 1-7, 9-11 and 27-31 under 35 U.S.C. §103(a) over U.S. Patent 6,324,067 to Nishiyama *et al.* (Nishiyama) in view of U.S. Patent 5,646,828 to Degani *et al.* (Degani). This rejection is rendered moot with respect to claim 2 and respectfully traversed with respect to the remaining claims. As discussed during the April 8 personal interview, claims 1 and 29, as amended, overcome Nishiyama and Degani. Withdrawal of the §103 rejection is respectfully requested.

The Office Action further rejects claim 8 under 35 U.S.C. §103(a) over Nishiyama in view of Degani and further in view of Plepys. This rejection is respectfully traversed.

As discussed during the April 8 personal interview, claim 1 as amended, from which claim 8 depends indirectly, overcomes Nishiyama and Degani. Because claim 1 would be allowable over Nishiyama and Degani, claim 8 should also be allowable. Withdrawal of the §103 rejection is respectfully requested.

For at least these reasons, Applicant respectfully asserts that the independent claims are now patentable over the applied references. The dependent claims are likewise patentable over the applied references for at least the reasons discussed as well as for the additional features they recite. Consequently, all the claims are in condition for allowance. Thus,

Applicant respectfully requests that the rejections under 35 U.S.C. §§102 and 103 be withdrawn.

II. Conclusion

In view of the foregoing amendments and remarks, Applicant respectfully submits that this application is in condition for allowance. Favorable reconsideration and prompt allowance are earnestly solicited.

Should the Examiner believe that anything further is desirable in order to place this application in even better condition for allowance, the Examiner is invited to contact Applicant's undersigned representative at the telephone number listed below.

Respectfully submitted,



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JAO:GWT/lrd

Attachment:
Appendix

Date: April 22, 2003

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<p>DEPOSIT ACCOUNT USE AUTHORIZATION Please grant any extension necessary for entry; Charge any fee due to our Deposit Account No. 15-0461</p>
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APPENDIX

Changes to Claims:

Claim 2 is canceled.

The following is a marked-up version of the amended claims:

1. (~~Twice~~Thrice Amended) A semiconductor device comprising:
 - a semiconductor chip on which a plurality of electrodes are formed;
 - a first flexible substrate in a tape form on which a wiring pattern is formed and on which the semiconductor chip is mounted;
 - a plurality of external terminals electrically connected to the electrodes with the wiring pattern interposed; and
 - a second flexible substrate in a tape form adhered to the first flexible substrate by a resin avoiding the semiconductor chip,wherein the second flexible substrate is formed of the same material as the first flexible substrate, and the first and second flexible substrates are of substantially the same thickness.
4. (Twice Amended) A semiconductor device comprising:
 - a semiconductor chip on which a plurality of electrodes are formed;
 - a first flexible substrate on which a wiring pattern is formed and on which the semiconductor chip is mounted;
 - a plurality of external terminals electrically connected to the electrodes with the wiring pattern interposed;
 - a second flexible substrate adhered to the first flexible substrate avoiding the semiconductor chip; and
 - a conductive layer which is formed between the first and second flexible substrates, wherein the first and second flexible substrates are of the same material and of substantially

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the same thickness as the wiring pattern, and the conductive layer is electrically insulated from the wiring pattern.

29. (Twice Amended) A semiconductor device comprising:

a semiconductor chip on which a plurality of electrodes are formed;

a first flexible substrate in a tape form on which a wiring pattern is formed and on which the semiconductor chip is mounted;

a plurality of external terminals electrically connected to the electrodes with the wiring pattern interposed; and

a second flexible substrate in a tape form adhered to the first flexible substrate by a resin avoiding the semiconductor chip,

wherein the second flexible substrate is formed of a material having a coefficient of thermal expansion substantially equal to a coefficient of thermal expansion of a material of the first flexible substrate, and the first and second flexible substrates are of substantially the same thickness.